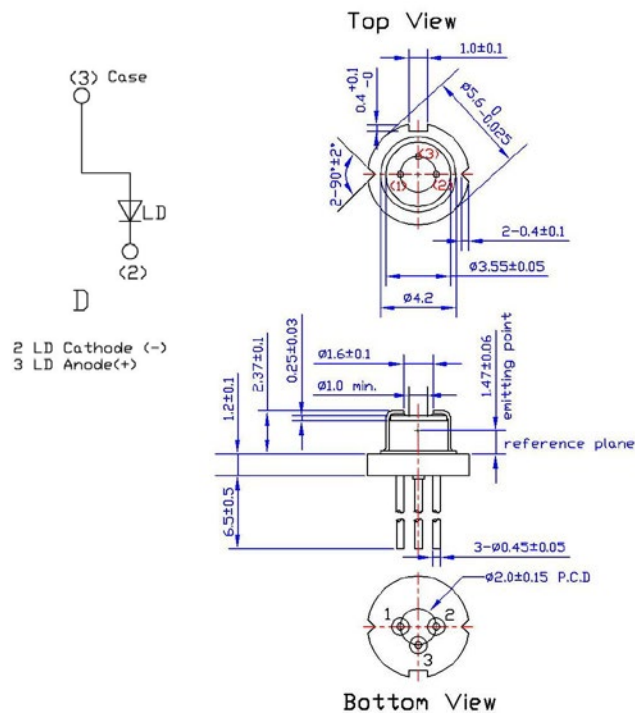


808nm IR Laser Diode LCU80B056D

■ Specifications

- (1) Device: Laser Diode
 (2) Structure: TO-18 (ϕ 5.6mm), With Pb free glass cap, no PD
 (3) Power Output: 200mW

■ External dimensions(Unit : mm)



■ Absolute Maximum Ratings(Tc=25°C)

Parameter	Symbols	Ratings	Units
Optical Output	Po	200	mW
Laser Diode Reverse Voltage	Vr	2	V
Operating Temperature (Case)	Top	-10~+50	°C
Storage Temperature	Tstg	-40~+85	°C

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808nm Laser Diode

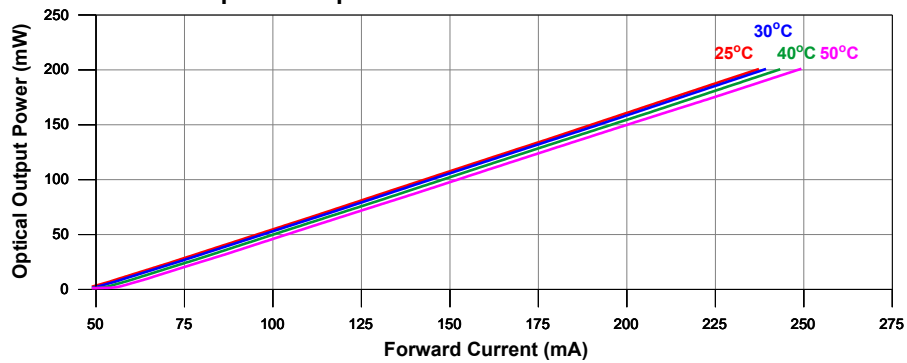
Electrical and Optical Characteristics (Tc=25°C)

Parameter	Symbols	Conditions	Min.	Typ.	Max.	Units
Threshold Current	I _{th}	-	-	50	70	mA
Operating Current	I _{op}	P _o =200mW	-	235	265	mA
Operating Voltage	V _{op}	-	-	1.8	1.95	Volts
Slope Efficiency	η	150mW-50mW	0.8	1.09	-	mW/mA
		I _{150mW} -I _{50mW}				
Beam Divergence (FWHM)	Parallel	θ //	-	7.5	12	deg.
	Perpendicular	θ ⊥	-	30	40	deg.
Lasing Wavelength*	λ	P _o =200mW	805	808	811	nm

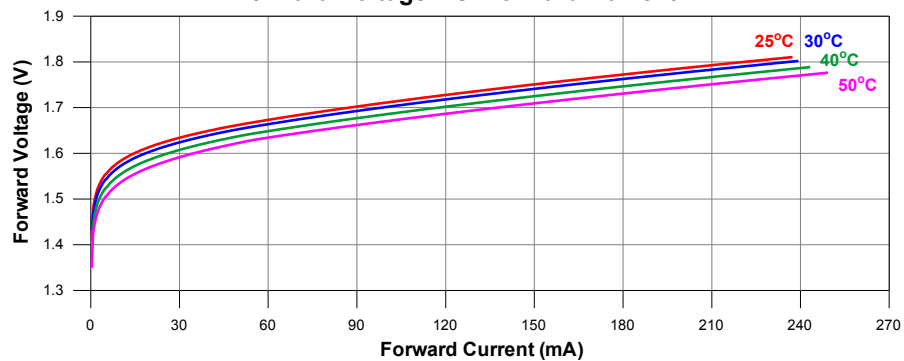
⊙ θ // and θ ⊥ are defined as the angle within which the intensity is 50% of the peak value.

Typical characteristic curves

Optical Output Power v.s. Forward Current

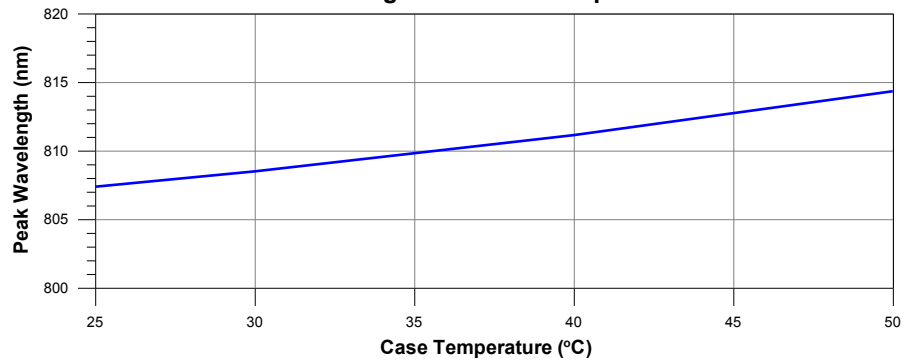


Forward Voltage v.s. Forward Current

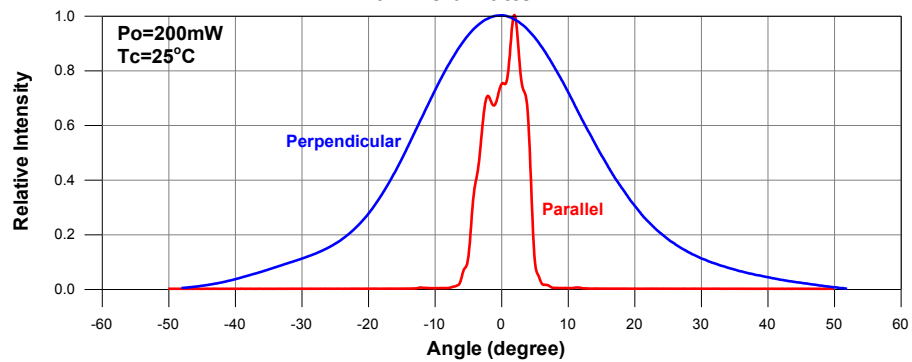


808nm Laser Diode

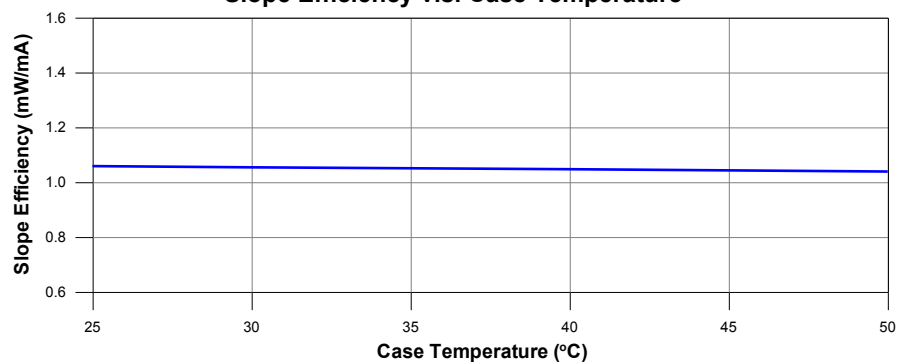
Peak Wavelength v.s. Case Temperature



Far-Field Pattern



Slope Efficiency v.s. Case Temperature



808nm Laser Diode

